

**IGBT-Wechselrichter / IGBT-inverter****Vorläufige Daten / preliminary data****Höchstzulässige Werte / maximum rated values**

|                                                                          |                                                                                                                      |                             |          |        |
|--------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------|-----------------------------|----------|--------|
| Kollektor-Emitter-Sperrspannung<br>collector-emitter voltage             | $T_{vj} = 25^{\circ}\text{C}$                                                                                        | $V_{CES}$                   | 1200     | V      |
| Kollektor-Dauergleichstrom<br>DC-collector current                       | $T_C = 80^{\circ}\text{C}, T_{vj} = 150^{\circ}\text{C}$<br>$T_C = 25^{\circ}\text{C}, T_{vj} = 150^{\circ}\text{C}$ | $I_{C\text{ nom}}$<br>$I_C$ | 15<br>25 | A<br>A |
| Periodischer Kollektor Spitzenstrom<br>repetitive peak collector current | $t_P = 1\text{ ms}$                                                                                                  | $I_{CRM}$                   | 30       | A      |
| Gesamt-Verlustleistung<br>total power dissipation                        | $T_C = 25^{\circ}\text{C}, T_{vj} = 150^{\circ}\text{C}$                                                             | $P_{tot}$                   | 105      | W      |
| Gate-Emitter-Spitzenspannung<br>gate-emitter peak voltage                |                                                                                                                      | $V_{GES}$                   | +/-20    | V      |

**Charakteristische Werte / characteristic values**

|                                                                              |                                                                                                                                                                                         |                                                                 | min.                | typ.           | max. |                                |
|------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------|---------------------|----------------|------|--------------------------------|
| Kollektor-Emitter Sättigungsspannung<br>collector-emitter saturation voltage | $I_C = 15\text{ A}, V_{GE} = 15\text{ V}$<br>$I_C = 15\text{ A}, V_{GE} = 15\text{ V}$                                                                                                  | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $V_{CE\text{ sat}}$ | 1,70<br>1,90   | 2,10 | V<br>V                         |
| Gate-Schwellenspannung<br>gate threshold voltage                             | $I_C = 0,60\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$                                                                                                                    |                                                                 | $V_{GEth}$          | 5,0            | 5,8  | 6,5 V                          |
| Gateladung<br>gate charge                                                    | $V_{GE} = -15\text{ V} \dots +15\text{ V}$                                                                                                                                              |                                                                 | $Q_G$               | 0,15           |      | $\mu\text{C}$                  |
| Interner Gatewiderstand<br>internal gate resistor                            | $T_{vj} = 25^{\circ}\text{C}$                                                                                                                                                           |                                                                 | $R_{Gint}$          | 0,0            |      | $\Omega$                       |
| Eingangskapazität<br>input capacitance                                       | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$                                                                                              |                                                                 | $C_{ies}$           | 1,10           |      | nF                             |
| Rückwirkungskapazität<br>reverse transfer capacitance                        | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$                                                                                              |                                                                 | $C_{res}$           | 0,04           |      | nF                             |
| Kollektor-Emitter Reststrom<br>collector-emitter cut-off current             | $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$                                                                                                              |                                                                 | $I_{CES}$           |                | 1,0  | mA                             |
| Gate-Emitter Reststrom<br>gate-emitter leakage current                       | $V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$                                                                                                                |                                                                 | $I_{GES}$           |                | 400  | nA                             |
| Einschaltverzögerungszeit (ind. Last)<br>turn-on delay time (inductive load) | $I_C = 15\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Gon} = 62\ \Omega$                                                                                      | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $t_{d\text{ on}}$   | 0,055<br>0,055 |      | $\mu\text{s}$<br>$\mu\text{s}$ |
| Anstiegszeit (induktive Last)<br>rise time (inductive load)                  | $I_C = 15\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Gon} = 62\ \Omega$                                                                                      | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $t_r$               | 0,02<br>0,025  |      | $\mu\text{s}$<br>$\mu\text{s}$ |
| Abschaltverzögerungszeit (ind. Last)<br>turn-off delay time (inductive load) | $I_C = 15\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Goff} = 62\ \Omega$                                                                                     | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $t_{d\text{ off}}$  | 0,37<br>0,47   |      | $\mu\text{s}$<br>$\mu\text{s}$ |
| Fallzeit (induktive Last)<br>fall time (inductive load)                      | $I_C = 15\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Goff} = 62\ \Omega$                                                                                     | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $t_f$               | 0,075<br>0,12  |      | $\mu\text{s}$<br>$\mu\text{s}$ |
| Einschaltverlustenergie pro Puls<br>turn-on energy loss per pulse            | $I_C = 15\text{ A}, V_{CE} = 600\text{ V}, L_S = 50\text{ nH}$<br>$V_{GE} = \pm 15\text{ V}, di/dt = 900\text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$<br>$R_{Gon} = 62\ \Omega$   | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $E_{on}$            | 1,60<br>2,15   |      | mJ<br>mJ                       |
| Abschaltverlustenergie pro Puls<br>turn-off energy loss per pulse            | $I_C = 15\text{ A}, V_{CE} = 600\text{ V}, L_S = 50\text{ nH}$<br>$V_{GE} = \pm 15\text{ V}, du/dt = 2600\text{ V}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$<br>$R_{Goff} = 62\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $E_{off}$           | 0,90<br>1,35   |      | mJ<br>mJ                       |
| Kurzschlussverhalten<br>SC data                                              | $V_{GE} \leq 15\text{ V}, V_{CC} = 900\text{ V}$<br>$V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$<br>$t_P \leq 10\ \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$                             |                                                                 | $I_{SC}$            | 60             |      | A                              |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case              | pro IGBT<br>per IGBT                                                                                                                                                                    |                                                                 | $R_{thJC}$          | 1,10           | 1,20 | K/W                            |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink            | pro IGBT / per IGBT<br>$\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$                                                 |                                                                 | $R_{thCH}$          | 1,05           |      | K/W                            |

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**Vorläufige Daten**  
**preliminary data****Diode-Wechselrichter / diode-inverter****Höchstzulässige Werte / maximum rated values**

|                                                                     |                                                                              |           |      |                      |
|---------------------------------------------------------------------|------------------------------------------------------------------------------|-----------|------|----------------------|
| Periodische Spitzensperrspannung<br>repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$                                                | $V_{RRM}$ | 1200 | V                    |
| Dauergleichstrom<br>DC forward current                              |                                                                              | $I_F$     | 15   | A                    |
| Periodischer Spitzenstrom<br>repetitive peak forward current        | $t_p = 1 \text{ ms}$                                                         | $I_{FRM}$ | 30   | A                    |
| Grenzlastintegral<br>$I^2t$ - value                                 | $V_R = 0 \text{ V}$ , $t_p = 10 \text{ ms}$ , $T_{vj} = 125^{\circ}\text{C}$ | $I^2t$    | 20,0 | $\text{A}^2\text{s}$ |

**Charakteristische Werte / characteristic values**

|                                                                   |                                                                                                                                                     |                                                                 |            | min. | typ.         | max. |                                |
|-------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------|------------|------|--------------|------|--------------------------------|
| Durchlassspannung<br>forward voltage                              | $I_F = 15 \text{ A}$ , $V_{GE} = 0 \text{ V}$<br>$I_F = 15 \text{ A}$ , $V_{GE} = 0 \text{ V}$                                                      | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $V_F$      |      | 1,90<br>2,00 | 2,50 | V<br>V                         |
| Rückstromspitze<br>peak reverse recovery current                  | $I_F = 15 \text{ A}$ , $-di_F/dt = 900 \text{ A}/\mu\text{s}$ ( $T_{vj}=125^{\circ}\text{C}$ )<br>$V_R = 600 \text{ V}$<br>$V_{GE} = -15 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $I_{RM}$   |      | 26,0<br>27,0 |      | A<br>A                         |
| Sperrverzögerungsladung<br>recovered charge                       | $I_F = 15 \text{ A}$ , $-di_F/dt = 900 \text{ A}/\mu\text{s}$ ( $T_{vj}=125^{\circ}\text{C}$ )<br>$V_R = 600 \text{ V}$<br>$V_{GE} = -15 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $Q_r$      |      | 1,60<br>2,90 |      | $\mu\text{C}$<br>$\mu\text{C}$ |
| Abschaltenergie pro Puls<br>reverse recovery energy               | $I_F = 15 \text{ A}$ , $-di_F/dt = 900 \text{ A}/\mu\text{s}$ ( $T_{vj}=125^{\circ}\text{C}$ )<br>$V_R = 600 \text{ V}$<br>$V_{GE} = -15 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $E_{rec}$  |      | 0,50<br>1,00 |      | mJ<br>mJ                       |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case   | pro Diode<br>per diode                                                                                                                              |                                                                 | $R_{thJC}$ |      | 1,75         | 1,95 | K/W                            |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink | pro Diode / per diode<br>$\lambda_{Paste} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$         |                                                                 | $R_{thCH}$ |      | 1,30         |      | K/W                            |

**Diode-Gleichrichter / diode-rectifier****Höchstzulässige Werte / maximum rated values**

|                                                                                     |                                                                                                                 |             |            |                                              |
|-------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------|-------------|------------|----------------------------------------------|
| Periodische Rückw. Spitzensperrspannung<br>repetitive peak reverse voltage          | $T_{vj} = 25^{\circ}\text{C}$                                                                                   | $V_{RRM}$   | 1600       | V                                            |
| Durchlassstrom Grenzeffektivwert pro Dio.<br>forward current RMS maximum per diode  | $T_C = 80^{\circ}\text{C}$                                                                                      | $I_{FRMSM}$ | 30         | A                                            |
| Gleichrichter Ausgang Grenzeffektivstrom<br>maximum RMS current at Rectifier output | $T_C = 80^{\circ}\text{C}$                                                                                      | $I_{RMSM}$  | 30         | A                                            |
| Stoßstrom Grenzwert<br>surge forward current                                        | $t_p = 10 \text{ ms}$ , $T_{vj} = 25^{\circ}\text{C}$<br>$t_p = 10 \text{ ms}$ , $T_{vj} = 150^{\circ}\text{C}$ | $I_{FSM}$   | 300<br>245 | A<br>A                                       |
| Grenzlastintegral<br>$I^2t$ - value                                                 | $t_p = 10 \text{ ms}$ , $T_{vj} = 25^{\circ}\text{C}$<br>$t_p = 10 \text{ ms}$ , $T_{vj} = 150^{\circ}\text{C}$ | $I^2t$      | 450<br>300 | $\text{A}^2\text{s}$<br>$\text{A}^2\text{s}$ |

**Charakteristische Werte / characteristic values**

|                                                                   |                                                                                                                                             |  |            | min. | typ. | max. |     |
|-------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------|--|------------|------|------|------|-----|
| Durchlassspannung<br>forward voltage                              | $T_{vj} = 150^{\circ}\text{C}$ , $I_F = 15 \text{ A}$                                                                                       |  | $V_F$      |      | 0,85 |      | V   |
| Sperrstrom<br>reverse current                                     | $T_{vj} = 150^{\circ}\text{C}$ , $V_R = 1600 \text{ V}$                                                                                     |  | $I_R$      |      | 2,00 |      | mA  |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case   | pro Diode<br>per diode                                                                                                                      |  | $R_{thJC}$ |      | 1,20 | 1,35 | K/W |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink | pro Diode / per diode<br>$\lambda_{Paste} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$ |  | $R_{thCH}$ |      | 1,15 |      | K/W |

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**Vorläufige Daten**  
**preliminary data****IGBT-Brems-Chopper / IGBT-brake-chopper****Höchstzulässige Werte / maximum rated values**

|                                                                          |                                                                                                                      |                     |          |        |
|--------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------|---------------------|----------|--------|
| Kollektor-Emitter-Sperrspannung<br>collector-emitter voltage             | $T_{vj} = 25^{\circ}\text{C}$                                                                                        | $V_{CES}$           | 1200     | V      |
| Kollektor-Dauergleichstrom<br>DC-collector current                       | $T_C = 80^{\circ}\text{C}, T_{vj} = 150^{\circ}\text{C}$<br>$T_C = 25^{\circ}\text{C}, T_{vj} = 150^{\circ}\text{C}$ | $I_{Cnom}$<br>$I_C$ | 15<br>25 | A<br>A |
| Periodischer Kollektor Spitzenstrom<br>repetitive peak collector current | $t_P = 1 \text{ ms}$                                                                                                 | $I_{CRM}$           | 30       | A      |
| Gesamt-Verlustleistung<br>total power dissipation                        | $T_C = 25^{\circ}\text{C}, T_{vj} = 150^{\circ}\text{C}$                                                             | $P_{tot}$           | 105      | W      |
| Gate-Emitter-Spitzenspannung<br>gate-emitter peak voltage                |                                                                                                                      | $V_{GES}$           | +/-20    | V      |

**Charakteristische Werte / characteristic values**

|                                                                              |                                                                                                                                                              |                                                                 | min.         | typ.           | max. |                                |
|------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------|--------------|----------------|------|--------------------------------|
| Kollektor-Emitter Sättigungsspannung<br>collector-emitter saturation voltage | $I_C = 15 \text{ A}, V_{GE} = 15 \text{ V}$<br>$I_C = 15 \text{ A}, V_{GE} = 15 \text{ V}$                                                                   | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $V_{CE sat}$ | 1,70<br>1,90   | 2,10 | V<br>V                         |
| Gate-Schwellenspannung<br>gate threshold voltage                             | $I_C = 0,60 \text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$                                                                                        |                                                                 | $V_{GEth}$   | 5,0            | 5,8  | 6,5 V                          |
| Gateladung<br>gate charge                                                    | $V_{GE} = -15 \text{ V} \dots +15 \text{ V}$                                                                                                                 |                                                                 | $Q_G$        | 0,15           |      | $\mu\text{C}$                  |
| Interner Gatewiderstand<br>internal gate resistor                            | $T_{vj} = 25^{\circ}\text{C}$                                                                                                                                |                                                                 | $R_{Gint}$   | 0,00           |      | $\Omega$                       |
| Eingangskapazität<br>input capacitance                                       | $f = 1 \text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$                                                                |                                                                 | $C_{ies}$    | 1,10           |      | nF                             |
| Rückwirkungskapazität<br>reverse transfer capacitance                        | $f = 1 \text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$                                                                |                                                                 | $C_{res}$    | 0,04           |      | nF                             |
| Kollektor-Emitter Reststrom<br>collector-emitter cut-off current             | $V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}, T_{vj} = 25^{\circ}\text{C}$                                                                                 |                                                                 | $I_{CES}$    |                | 1,0  | mA                             |
| Gate-Emitter Reststrom<br>gate-emitter leakage current                       | $V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}, T_{vj} = 25^{\circ}\text{C}$                                                                                   |                                                                 | $I_{GES}$    |                | 400  | nA                             |
| Einschaltverzögerungszeit (ind. Last)<br>turn-on delay time (inductive load) | $I_C = 15 \text{ A}, V_{CE} = 600 \text{ V}$<br>$V_{GE} = \pm 15 \text{ V}$<br>$R_{Gon} = 62 \Omega$                                                         | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $t_{d on}$   | 0,055<br>0,055 |      | $\mu\text{s}$<br>$\mu\text{s}$ |
| Anstiegszeit (induktive Last)<br>rise time (inductive load)                  | $I_C = 15 \text{ A}, V_{CE} = 600 \text{ V}$<br>$V_{GE} = \pm 15 \text{ V}$<br>$R_{Gon} = 62 \Omega$                                                         | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $t_r$        | 0,02<br>0,025  |      | $\mu\text{s}$<br>$\mu\text{s}$ |
| Abschaltverzögerungszeit (ind. Last)<br>turn-off delay time (inductive load) | $I_C = 15 \text{ A}, V_{CE} = 600 \text{ V}$<br>$V_{GE} = \pm 15 \text{ V}$<br>$R_{Goff} = 62 \Omega$                                                        | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $t_{d off}$  | 0,37<br>0,47   |      | $\mu\text{s}$<br>$\mu\text{s}$ |
| Fallzeit (induktive Last)<br>fall time (inductive load)                      | $I_C = 15 \text{ A}, V_{CE} = 600 \text{ V}$<br>$V_{GE} = \pm 15 \text{ V}$<br>$R_{Goff} = 62 \Omega$                                                        | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $t_f$        | 0,075<br>0,12  |      | $\mu\text{s}$<br>$\mu\text{s}$ |
| Einschaltverlustenergie pro Puls<br>turn-on energy loss per pulse            | $I_C = 15 \text{ A}, V_{CE} = 600 \text{ V}$<br>$V_{GE} = \pm 15 \text{ V}$<br>$R_{Gon} = 62 \Omega$                                                         | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $E_{on}$     | 1,60<br>2,15   |      | mJ<br>mJ                       |
| Abschaltverlustenergie pro Puls<br>turn-off energy loss per pulse            | $I_C = 15 \text{ A}, V_{CE} = 600 \text{ V}$<br>$V_{GE} = \pm 15 \text{ V}$<br>$R_{Goff} = 62 \Omega$                                                        | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $E_{off}$    | 0,90<br>1,35   |      | mJ<br>mJ                       |
| Kurzschlussverhalten<br>SC data                                              | $V_{GE} \leq 15 \text{ V}, V_{CC} = 900 \text{ V}$<br>$V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$<br>$t_P \leq 10 \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$ |                                                                 | $I_{sc}$     | 60             |      | A                              |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case              | pro IGBT<br>per IGBT                                                                                                                                         |                                                                 | $R_{thJC}$   | 1,10           | 1,20 | K/W                            |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink            | pro IGBT / per IGBT<br>$\lambda_{Paste} = 1 \text{ W}/(\text{m} \cdot \text{K}) / \lambda_{grease} = 1 \text{ W}/(\text{m} \cdot \text{K})$                  |                                                                 | $R_{thCH}$   | 1,05           |      | K/W                            |

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**Vorläufige Daten**  
**preliminary data****Diode-Brems-Chopper / Diode-brake-chopper****Höchstzulässige Werte / maximum rated values**

|                                                                |                                                                        |           |      |                      |
|----------------------------------------------------------------|------------------------------------------------------------------------|-----------|------|----------------------|
| Periodische Spitzenspernung<br>repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$                                          | $V_{RRM}$ | 1200 | V                    |
| Dauergleichstrom<br>DC forward current                         |                                                                        | $I_F$     | 10   | A                    |
| Periodischer Spitzenstrom<br>repetitive peak forw. current     | $t_p = 1 \text{ ms}$                                                   | $I_{FRM}$ | 20   | A                    |
| Grenzlastintegral<br>$I^2t$ - value                            | $V_R = 0 \text{ V}, t_p = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$ | $I^2t$    | 11,0 | $\text{A}^2\text{s}$ |

**Charakteristische Werte / characteristic values**

|                                                                   |                                                                                                                                              |                                                                 |            | min. | typ.         | max. |                                |
|-------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------|------------|------|--------------|------|--------------------------------|
| Durchlassspannung<br>forward voltage                              | $I_F = 10 \text{ A}, V_{GE} = 0 \text{ V}$<br>$I_F = 10 \text{ A}, V_{GE} = 0 \text{ V}$                                                     | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $V_F$      |      | 1,85<br>1,90 | 2,30 | V<br>V                         |
| Rückstromspitze<br>peak reverse recovery current                  | $I_F = 10 \text{ A}, -di_F/dt = 200 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$<br>$V_R = 600 \text{ V}$<br>$V_{GE} = -15 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $I_{RM}$   |      | 12,0<br>12,0 |      | A<br>A                         |
| Sperrverzögerungsladung<br>recovered charge                       | $I_F = 10 \text{ A}, -di_F/dt = 200 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$<br>$V_R = 600 \text{ V}$<br>$V_{GE} = -15 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $Q_r$      |      | 1,00<br>1,75 |      | $\mu\text{C}$<br>$\mu\text{C}$ |
| Abschaltenergie pro Puls<br>reverse recovery energy               | $I_F = 10 \text{ A}, -di_F/dt = 200 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$<br>$V_R = 600 \text{ V}$<br>$V_{GE} = -15 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$ | $E_{rec}$  |      | 0,55<br>0,85 |      | mJ<br>mJ                       |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case   | pro Diode<br>per diode                                                                                                                       |                                                                 | $R_{thJC}$ |      | 2,10         | 2,35 | K/W                            |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink | pro Diode / per diode<br>$\lambda_{Paste} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$    |                                                                 | $R_{thCH}$ |      | 1,35         |      | K/W                            |

**NTC-Widerstand / NTC-thermistor****Charakteristische Werte / characteristic values**

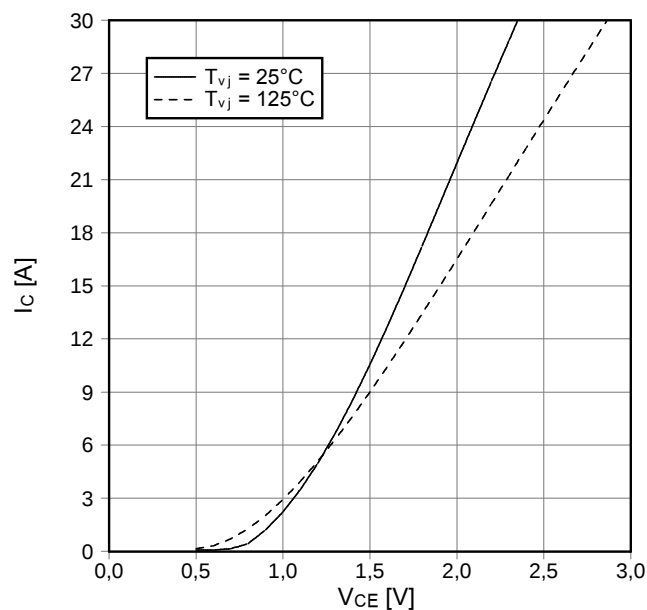
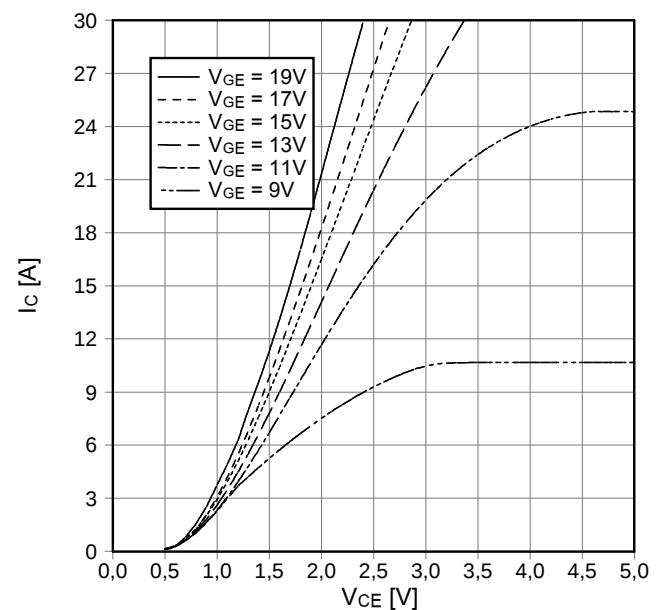
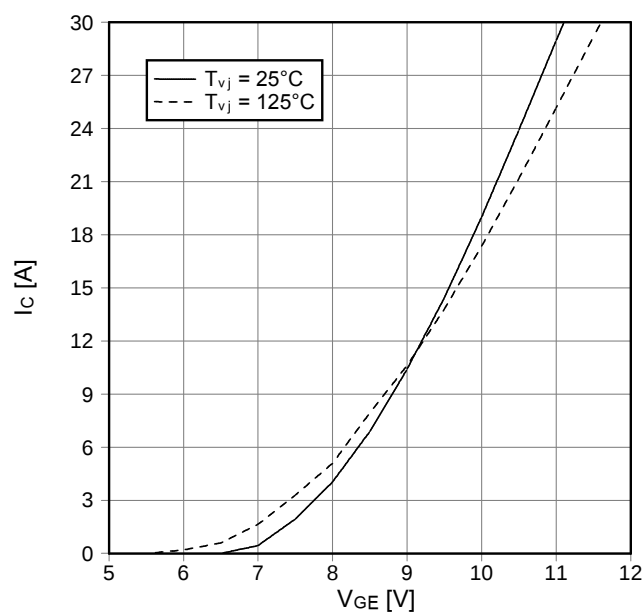
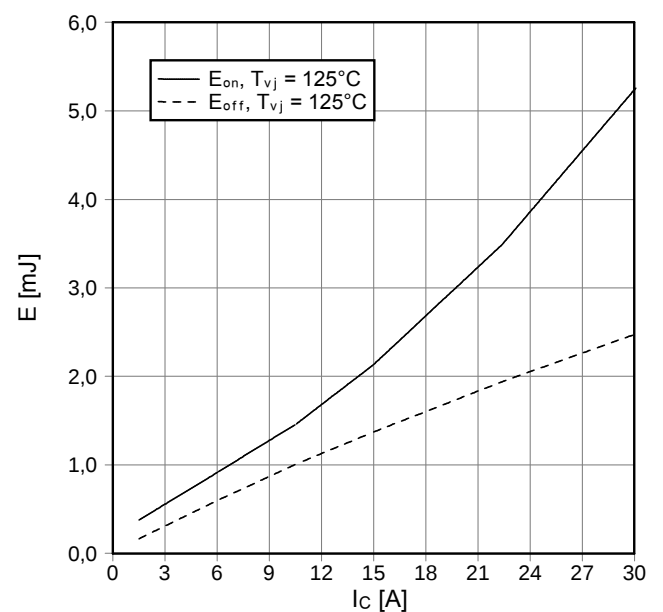
|                                                    |                                                               |              |    | min. | typ. | max. |            |
|----------------------------------------------------|---------------------------------------------------------------|--------------|----|------|------|------|------------|
| Nennwiderstand<br>rated resistance                 | $T_C = 25^{\circ}\text{C}$                                    | $R_{25}$     |    |      | 5,00 |      | k $\Omega$ |
| Abweichung von $R_{100}$<br>deviation of $R_{100}$ | $T_C = 100^{\circ}\text{C}, R_{100} = 493 \Omega$             | $\Delta R/R$ | -5 |      |      | 5    | %          |
| Verlustleistung<br>power dissipation               | $T_C = 25^{\circ}\text{C}$                                    | $P_{25}$     |    |      |      | 20,0 | mW         |
| B-Wert<br>B-value                                  | $R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$ | $B_{25/50}$  |    |      | 3375 |      | K          |

**Vorläufige Daten**  
**preliminary data****Modul / module**

|                                                                                              |                                                                                         |                                              |                                |              |
|----------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------|----------------------------------------------|--------------------------------|--------------|
| Isolations-Prüfspannung<br>insulation test voltage                                           | RMS, f = 50 Hz, t = 1 min.                                                              | V <sub>ISO</sub>                             | 2,5                            | kV           |
| Material für innere Isolation<br>material for internal insulation                            |                                                                                         |                                              | Al <sub>2</sub> O <sub>3</sub> |              |
| Kriechstrecke<br>creepage distance                                                           | Kontakt - Kühlkörper / terminal to heatsink<br>Kontakt - Kontakt / terminal to terminal |                                              | 11,5<br>6,3                    | mm           |
| Luftstrecke<br>clearance distance                                                            | Kontakt - Kühlkörper / terminal to heatsink<br>Kontakt - Kontakt / terminal to terminal |                                              | 10,0<br>5,0                    | mm           |
| Vergleichszahl der Kriechwegbildung<br>comparative tracking index                            |                                                                                         | CTI                                          | > 225                          |              |
| Modulinduktivität<br>stray inductance module                                                 |                                                                                         | L <sub>sCE</sub>                             | min. 30                        | typ. max. nH |
| Modulleitungswiderstand,<br>Anschlüsse - Chip<br>module lead resistance,<br>terminals - chip | T <sub>C</sub> = 25°C, pro Schalter / per switch                                        | R <sub>CC'+EE'</sub><br>R <sub>AA'+CC'</sub> | 8,00<br>6,00                   | mΩ           |
| Höchstzulässige Sperrschichttemperatur<br>maximum junction temperature                       | Wechselrichter, Brems-Chopper / Inverter, Brake-Chopper                                 | T <sub>vj max</sub>                          |                                | 150 °C       |
| Temperatur im Schaltbetrieb<br>temperature under switching conditions                        | Wechselrichter, Brems-Chopper / Inverter, Brake-Chopper                                 | T <sub>vj op</sub>                           | -40                            | 125 °C       |
| Lagertemperatur<br>storage temperature                                                       |                                                                                         | T <sub>stg</sub>                             | -40                            | 125 °C       |
| Anpresskraft für mech. Bef. pro Feder<br>mounting force per clamp                            |                                                                                         | F                                            | 20                             | - 50 N       |
| Gewicht<br>weight                                                                            |                                                                                         | G                                            | 24                             | g            |

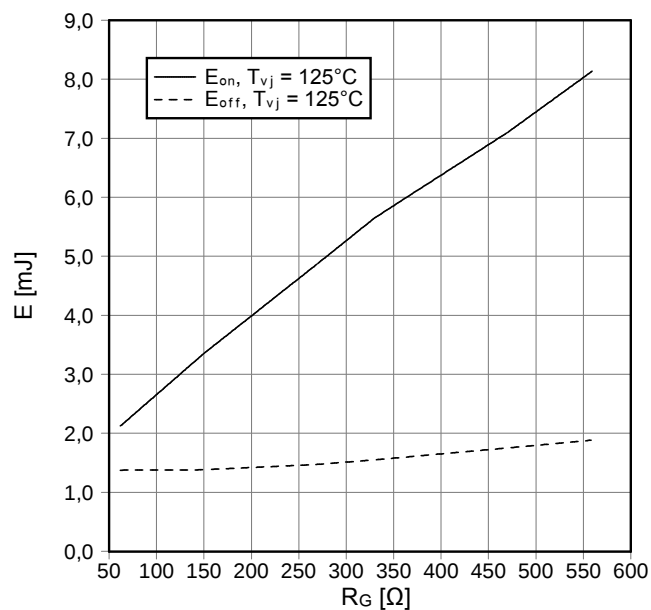
Der Strom im Dauerbetrieb ist auf 30 A pro Anschlusspin begrenzt.  
The current under continuous operation is limited to 30 A rms per connector pin.

|                              |                                 |
|------------------------------|---------------------------------|
| prepared by: Daniel Kreuzer  | date of publication: 2006-10-11 |
| approved by: Marc Buschkühle | revision: 2.0                   |

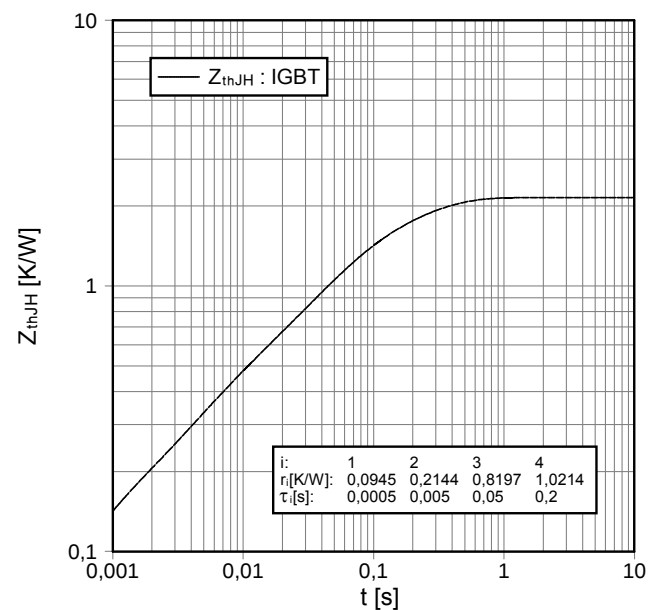
**Vorläufige Daten**  
**preliminary data**
**Ausgangskennlinie IGBT-Wechselr. (typisch)**  
**output characteristic IGBT-inverter (typical)**
 $I_C = f(V_{CE})$   
 $V_{GE} = 15 \text{ V}$ 

**Ausgangskennlinienfeld IGBT-Wechselr. (typisch)**  
**output characteristic IGBT-inverter (typical)**
 $I_C = f(V_{CE})$   
 $T_{vj} = 125^\circ\text{C}$ 

**Übertragungscharakteristik IGBT-Wechselr. (typisch)**  
**transfer characteristic IGBT-inverter (typical)**
 $I_C = f(V_{GE})$   
 $V_{CE} = 20 \text{ V}$ 

**Schaltverluste IGBT-Wechselr. (typisch)**  
**switching losses IGBT-inverter (typical)**
 $E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$   
 $V_{GE} = \pm 15 \text{ V}$ ,  $R_{Gon} = 62 \Omega$ ,  $R_{Goff} = 62 \Omega$ ,  $V_{CE} = 600 \text{ V}$ 


Vorläufige Daten  
preliminary data

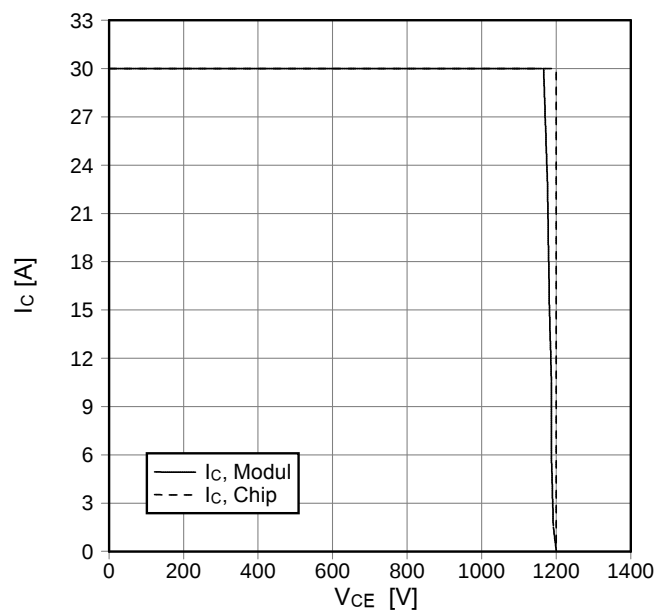
Schaltverluste IGBT-Wechselr. (typisch)  
switching losses IGBT-Inverter (typical)  
 $E_{on} = f(R_G)$ ,  $E_{off} = f(R_G)$   
 $V_{GE} = \pm 15 \text{ V}$ ,  $I_C = 15 \text{ A}$ ,  $V_{CE} = 600 \text{ V}$



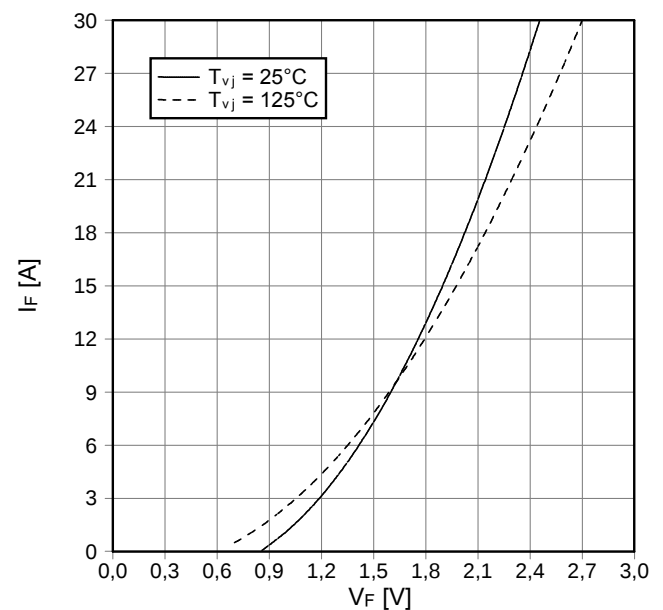
Transienter Wärmewiderstand IGBT-Wechselr.  
transient thermal impedance IGBT-inverter  
 $Z_{thJH} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT-Wr. (RBSOA)  
reverse bias safe operating area IGBT-inv. (RBSOA)  
 $I_C = f(V_{CE})$   
 $V_{GE} = \pm 15 \text{ V}$ ,  $R_{Goff} = 62 \Omega$ ,  $T_{vj} = 125^\circ\text{C}$

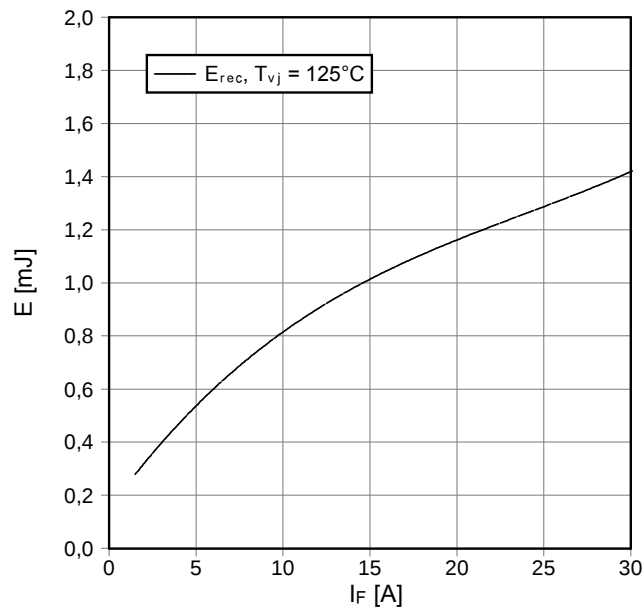


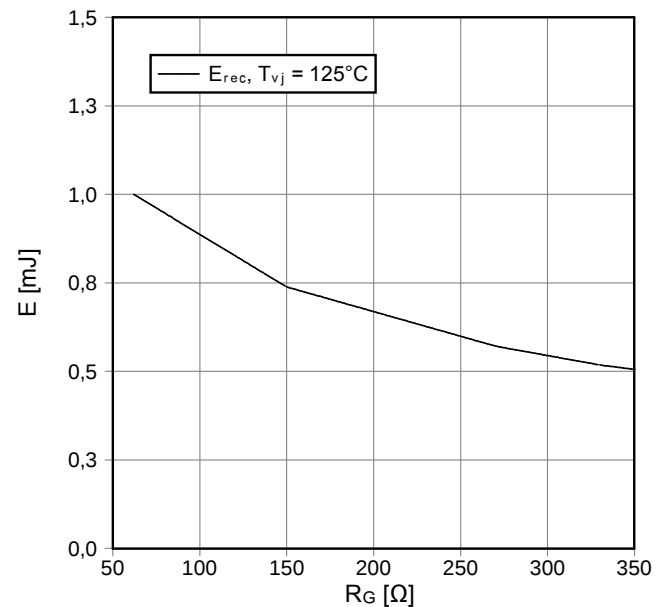
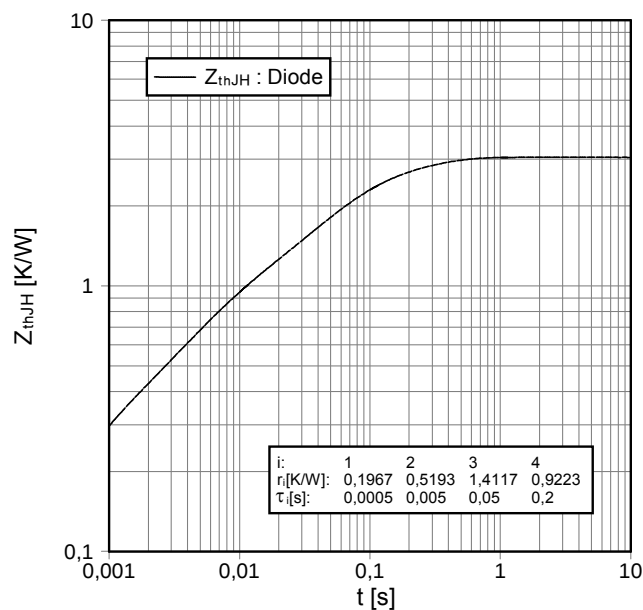
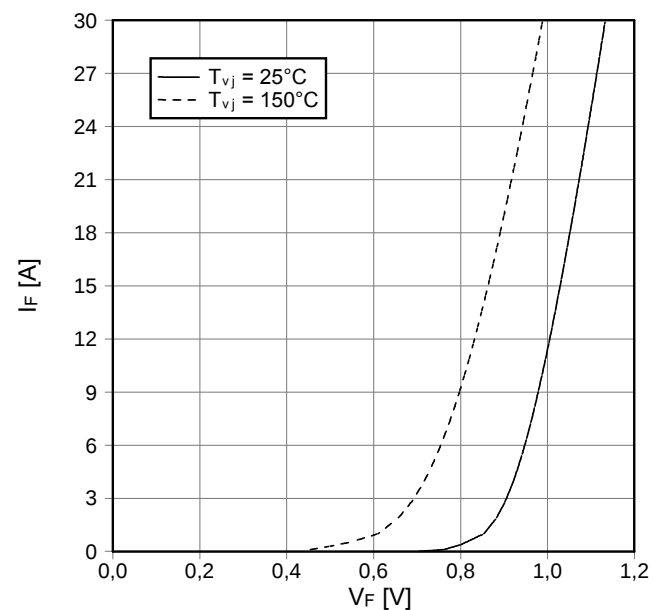
Durchlasskennlinie der Diode-Wechselr. (typisch)  
forward characteristic of diode-inverter (typical)  
 $I_F = f(V_F)$

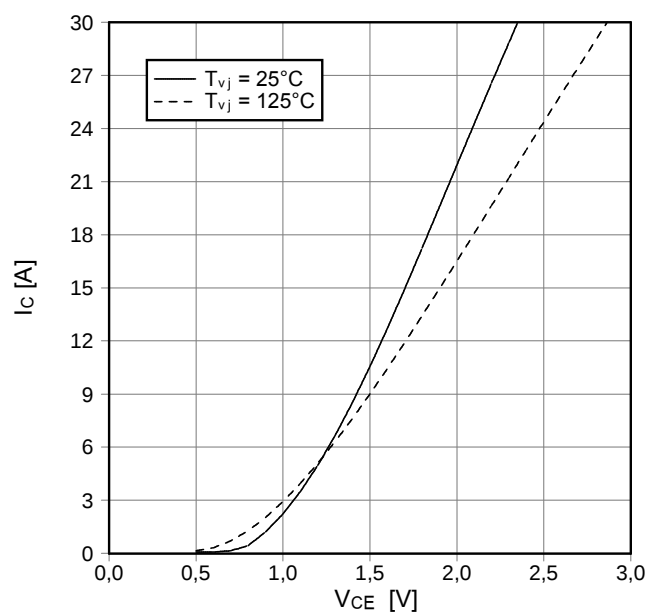
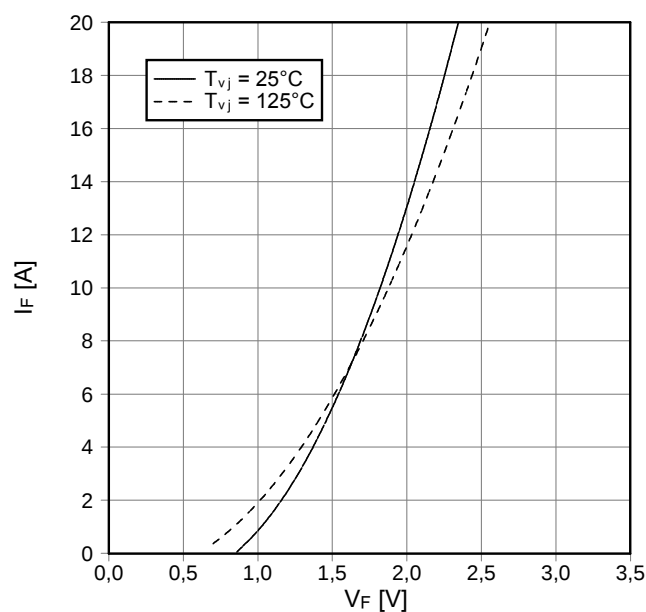
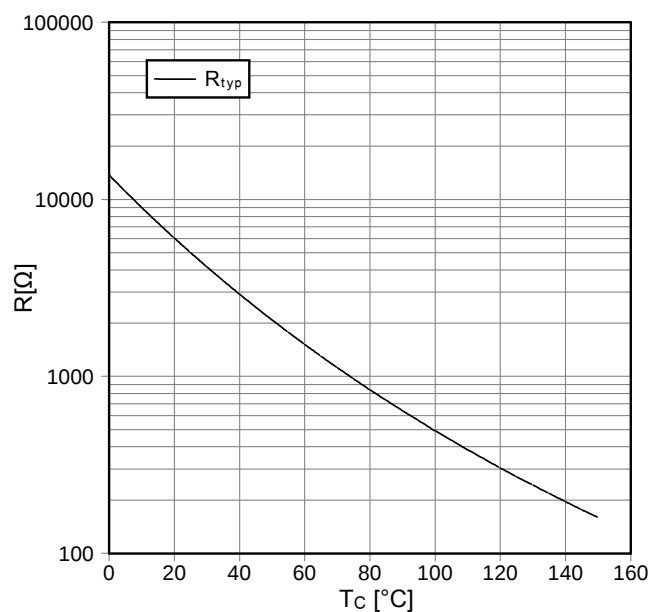


Vorläufige Daten  
preliminary data

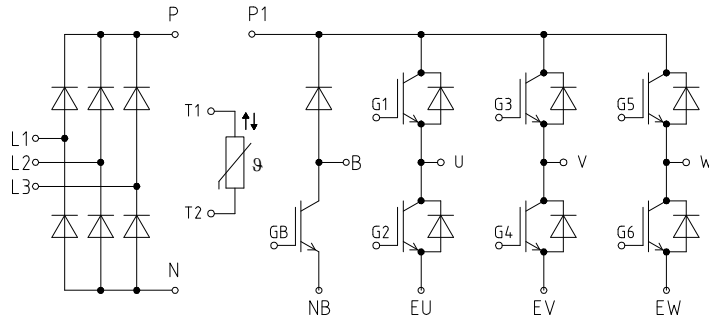
Schaltverluste Diode-Wechselr. (typisch)  
switching losses diode-inverter (typical)

 $E_{rec} = f(I_F)$   
 $R_{Gon} = 62 \Omega$ ,  $V_{CE} = 600 V$ 

Schaltverluste Diode-Wechselr. (typisch)  
switching losses diode-inverter (typical)

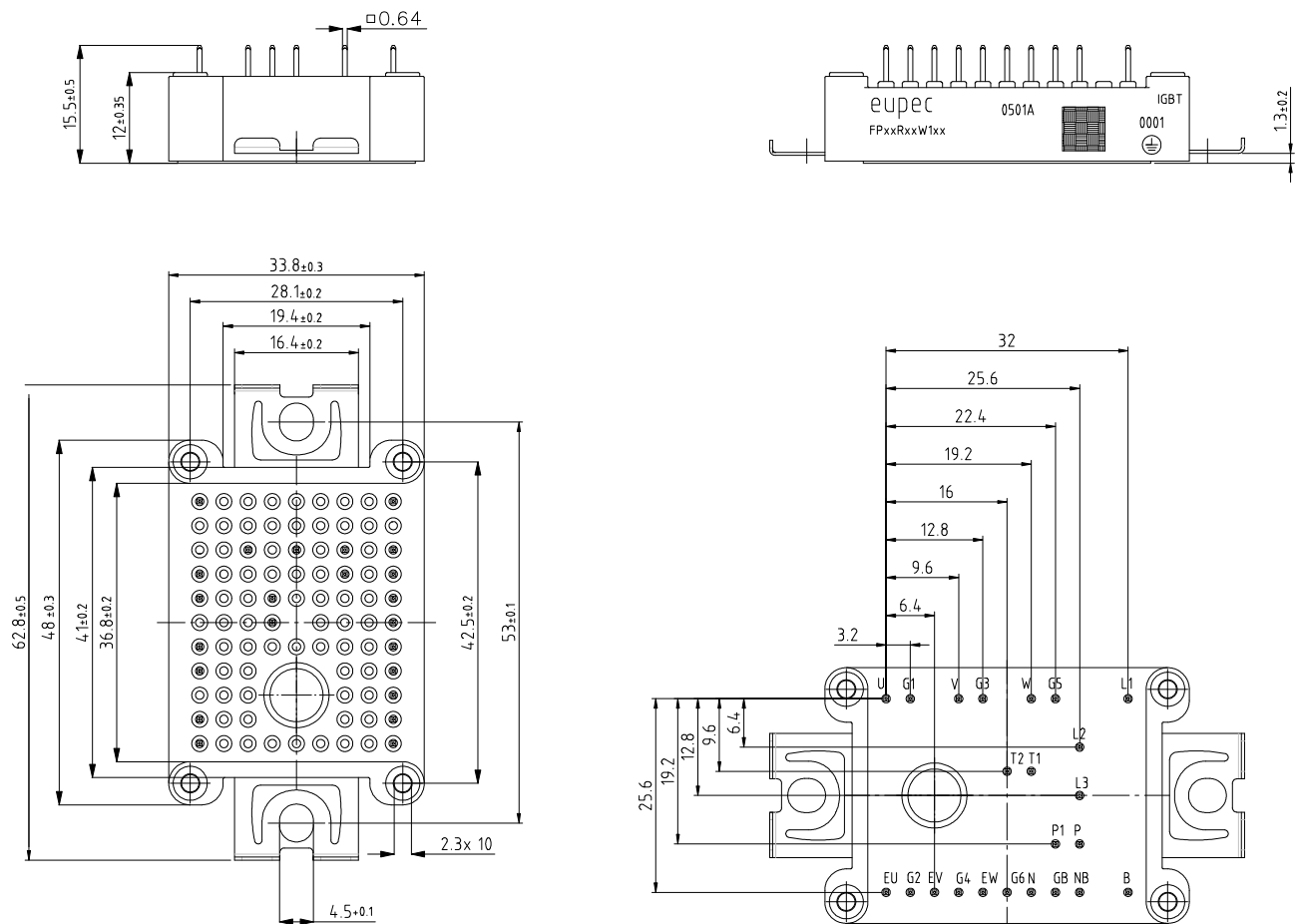
 $E_{rec} = f(R_G)$   
 $I_F = 15 A$ ,  $V_{CE} = 600 V$ 

Transienter Wärmewiderstand Diode-Wechselr.  
transient thermal impedance diode-inverter  
 $Z_{thJH} = f(t)$ 

Durchlasskennlinie der Diode-Gleichrichter (typisch)  
forward characteristic of diode-rectifier (typical)  
 $I_F = f(V_F)$ 


**Vorläufige Daten**  
**preliminary data**
**Ausgangskennlinie IGBT-Brems-Copper (typisch)**  
**output characteristic IGBT-brake-chopper (typical)**
 $I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$ 

**Durchlasskennlinie der Diode-Brems-Chopper (typisch)**  
**forward characteristic of diode-brake-chopper (typical)**
 $I_F = f(V_F)$ 

**NTC-Temperaturkennlinie (typisch)**  
**NTC-temperature characteristic (typical)**  
 $R = f(T)$ 


## Schaltplan / circuit diagram



## Gehäuseabmessungen / package outlines



**Vorläufige Daten**  
**preliminary data****Nutzungsbedingungen**

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- the conclusion of Quality Agreements;
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